In the Claims:

Please amend claims 10, 28, and 29. The claims are as follows:

Claims 1-9 (CANCELED)

10. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps ~~performed in the indicated sequential order~~:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;

forming a mineral layer on the metallic plate after the step of providing a metallic plate is performed; and

forming an adhesion promoter layer on the mineral layer after the step of forming a mineral layer is performed.

11. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a mineral selected from the group consisting of silicon dioxide, silicon nitride, and silicon carbide.

12. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a thickness between about 50 angstroms and about 2000 angstroms.

13. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes sputtering the mineral layer on a clean surface of the metallic plate.

14. (PREVIOUSLY PRESENTED) The method of claim 10, wherein providing the metallic plate includes providing the metallic plate having a metallic substance selected from the group consisting of stainless steel, aluminum, titanium, copper, copper coated with nickel, and copper coated with chrome.

15. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter selected from the group consisting of a titanate, a zirconate, and an aluminate.

16. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having a silane from the group consisting of 3-glycidoxypropyltrimethoxysilane, 3-glycidoxypropyltriethoxysilane, 3-(2-aminoethyl)propyltrimethoxysilane, and 3-(2-aminoethyl)propyltrmethoxysilane.

17. (ORIGINAL) The method of claim 10, further comprising:

providing an electronic assembly;

providing an adhesive material;

coupling the metallic plate to the electronic assembly by interfacing the adhesive material

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between the adhesion promoter layer and the electronic assembly;

providing an electronic carrier;

coupling the electronic assembly to the electronic carrier; and

coupling the metallic plate to the electronic carrier by interfacing the adhesive material between the adhesion promoter layer and the electronic carrier.

18. (PREVIOUSLY PRESENTED) The method of claim 17, wherein providing the adhesive material includes providing the adhesive material having a structural epoxy adhesive.

19. (PREVIOUSLY PRESENTED) The method of claim 17, wherein providing the metallic plate includes providing the metallic plate having a coefficient of thermal expansion (CTE) that exceeds a CTE of the electronic assembly.

20. (PREVIOUSLY PRESENTED) The method of claim 10, further comprising bonding the adhesion promoter layer to a structural adhesive.

21. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the adhesion promoter layer has a thickness between 1 monolayer and about 50 monolayers.

22. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming an the adhesion promoter layer includes forming the adhesion promoter layer comprising a chemical compound in crystalline form.

23. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer comprising a chemical compound in amorphous form.

24. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer comprises forming the mineral layer covering an edge surface of the metallic plate and a portion of a top surface of the metallic plate.

25. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a thickness between about 100 angstroms and about 1000 angstroms.

26. (Canceled)

27. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter comprising a silane.

28. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed ~~in the indicated sequential order~~:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed

to an ambient atmosphere;

bonding a mineral layer to the metallic plate after the step of providing a metallic plate is performed; and

covalently bonding an adhesion promoter layer to the mineral layer after the step of bonding a mineral layer is performed.

29. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed ~~in the indicated sequential order~~:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;

bonding a mineral layer to the metallic plate after the step of providing a metallic plate is performed; and

bonding an adhesion promoter layer to the mineral layer such that said bonding to the mineral layer is moisture resistant, after the step of bonding a mineral layer is performed.

30. (PREVIOUSLY ADDED) The method of claim 10, wherein providing the metallic plate includes providing the metallic plate having a metallic substance selected from the group consisting of stainless steel, titanium, copper, copper coated with nickel, and copper coated with chrome.